Application No. 09/500,288

GaN substrate with crack prevention and special grow method to reduce compressive strain and thermal relief

Search	L No.	Hits	Text Search		
					Data Bases
BRS	L Li	270769	(led (light adj emitting adj device))	1	USPAT: EPO; JI
			(ver (ver day emitting ady device))	6/21/01 11:43	Derwent; IBM T
BRS	L2	1152	I and gan		USPAT; EPO; JF
			S and Built	6/21/01 11:43	Derwent; IBM TI
BRS	L3	4	2 and (crack adj prevention)		USPAT; EPO; JP
			(man adj prevention)	6/21/01 11:44	Derwent: IBM TI
BRS	L4	15	2 and (compressive adj strain)		USPAT: EPO; JP
			(sempressive adj strain)	6/21/01 11:53	Derwent; IBM TI
BRS	L2	49	1 and (concave convex)		USPAT; EPO; JP
			and (concave convex)	6/21/01 13:03	Derwent: IBM TD
		}	((led (light adj emitting adj device))) and		
BRS	L7	77	((gan (gallium adj nitride)) adj substrate)		USPAT; EPO; JPO
1			(Le de la	6/21/01 13:59	Derwent; IBM TD
BRS	L8	30	7 and (single adj crystal)	(2112)	USPAT: EPO: JPO
1			grand allowers	6/21/01 13:59	Derwent; IBM TD
BRS	L9	5 8	8 and compressive adj strain	6/21/01 13:59	USPAT; EPO: JPC
					Derwent: IBM TD

Search Result

USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	
j]		Method of growing nitride	Cusul	CI/Sub	Inventor
	1		semiconductors, nitride semiconductor	Į.	1	1
	1 1		substrate and nitride semiconductor	1	117/106 - 117/052	1
US 6153010 A	20001128	35	device	117/95	117/106 ; 117/952 117/97	
			Extended wavelength strained layer	11//93	257/17 ; 257/18 :	Kiyoku, Hiroyuki . et al.
	1 1		lasers having strain compensated	1		ł
US 5825796 A	19981020	32	layers	372/45	257/190 ; 257/94 ; 372/46	
ı				372743	257/190 ; 257/196	Jewell, Jack L., et al.
	į l					
	1		Gallium nitride type compound	1	257/201 ; 257/615	· [
	1 1	ı	semiconductor light-emitting device		257/618: 257/622	:
	1 1	1	having buffer layer with non-flat		257/623 ; 257/76 ;	1
US 6091083 A	20000718		surface	255/50	257/97; 372/45;	
			Three-dimensional picture image display	257/79	372/46	Hata, Toshio, et al.
US 6057878 A	20000502	36	apparatus	i	1	
		- 50	Integrated optical control element and a	348/56	348/51	Ogiwara, Akifumi, et al.
	1	Į,		Į		
	'	1	optical integrated circuit element and	1		ł
	1	ſ.		1		1
IS 5838854 A	19981117	501	optical integrated circuit device using he same			
			Semiconductor light emitting element	385/50	359/124	Taneya. Mototaka . et al.
JS 5787104 A	19980728	44	and method for fabrical		1	
JS	11100120	7710	and method for fabricating the same	372/43	372/45	Kamiyama, Satoshi . et al.
0010002048	1	1,	ight amitting to 1			
11		26	light-emitting device using group III			Koike, Masavoshi,
		2011	itride group compound semiconductor			Yamakazi, Shiro , et al.
	1	[.,	emiconductor light emitting device with			
		a	n active layer made of			
S 6072197 A	20000606	12/50	emiconductor having uniaxial		257/627 : 257/628 :	
	2000000	42 ai	nisotropy	257/103	257/94 : 257/98	Horino, Kazuhiko , et al
S 5689123 A	19971118		I-V aresenide-nitride semiconductor		257/18:257/184:	tur direct, et ar
	1/2/1110	21Jm	aterials and devices	257/190	257/201 . 257/22	Major. Jo S., et al.
		$-\!\!+\!\!-$				
						
		-+				
		$-\!\!+\!\!$				

Application No. <u>09/500,288</u>

GaN substrate with crack prevention and special grow method to reduce compressive strain and thermal relief

6/21/01 East Search Data Bases Search L No. Hits Text Search ((led (light adj emitting adj device))) and USPAT; EPO; JPO: 6/21/01 14:58 BRS L7 (gan (gallium adj nitride)) Derwent: IBM TDB USPAT; EPO; JPO; 6/21/01 14:58 Derwent; IBM TDB BRS 292 7 and single adj crystal 1.8 USPAT; EPO; JPO; L9 Derwent; IBM TDB 6/21/01 14:58 BRS 8 and compressive adj strain USPAT; EPO; JPO: 8 and (coefficient near (thermal adj BRS L10 41 expansion)) 6/21/01 14:59 Derwent: IBM TDB USPAT: EPO: JPO: 6/21/01 15:00 Derwent: IBM TDB BRS 10 and lateral adj growth Π

USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
					117/952 : 257/103 :	
					257/13; 257/76;	
			Method for forming GaN semiconductor		372/43 ; 372/44 ;	
			single crystal substrate and GaN diode		438/47; 438/481;	
US 6177292 B1	20010123		with the substrate	438/46	438/493	Hong, Chang-Hee, et al.
23 0177292 DT	20010123	10	with the substrate	150/10	1301173	Trong trong trong
						
	-					
						-
-					 	· · · · · · · · · · · · · · · · · · ·
					 	·· ·
					 	
					 	